

## VII. Switching Diode

## SMD Type (SOT-23) BAV70

#### (Package: SOT-23) SOT-23 DIM Min Max **FEATURES** 0.37 0.51 В 1.20 1.40 С 2.10 2.64 · Fast switching speed D 0.89 1.03 · For general purpose switching applications Е 0.45 0.60 · High conductance 1.78 2.05 G · Low current leakage Η 2.80 3.04 · Small outline surface mount package 0.10 0.013 • RoHS compliant/Green EMC 0.90 1.11 0.45 0.60 0.09 0.18 All Dimensions in mm **DEVICE MARKING CODE** BAV70: A4 Case: SOT-23 Dimensions in millimeters TOP VIEW

### **Ratings & Electrical Characteristics**

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20%.

Maximum ratings

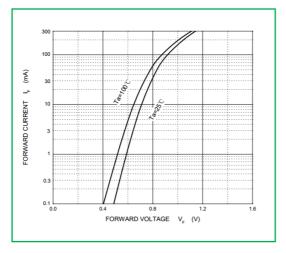
Symbol	Parameter	Value	Units
VR	Reverse voltage	75	Volts
lo	Average rectified output current	150	mA
PD	Power dissipation	225	mW
IFSM	Peak forward surge current @t=1.0s Non-repetitive	1.0	А
Tj	Junction temperature	150	°C
Tstg	Storage temperature	-55 to 150	$^{\circ}\mathbb{C}$
Rth	Thermal resistance	357	°C/W

#### **Electrical characteristics**

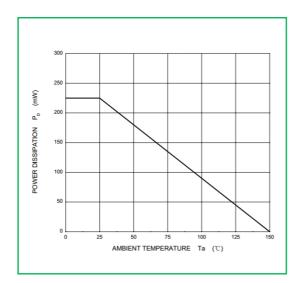
Symbol	Parameter	Test conditions	Min	Max	Units
VF	Forward voltage	I=1mA	-	0.715	Volts
		I⊧=10mA	-	0.855	
		I⊧=50mA	-	1.000	
		I <sub>F</sub> =150mA	-	1.250	
V <sub>(BR)R</sub>	Reverse breakdown voltage	IR=100µA	75	-	Volts
lr	Reverse voltage leakage current	V <sub>R</sub> =75V	-	2.5	μΑ
		V <sub>R</sub> =75V Ta=150°C	-	50	μA
Cj	Typical junction capacitance	V <sub>R</sub> =0V , f=1.0MHz	-	2	РF
Trr	Reverse recovery time	I <sub>F</sub> =10mA , $V_R$ =0 $V$ , $R_L$ =100 $\Omega$	-	4	ns



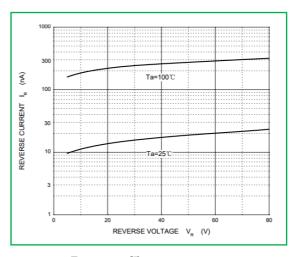
# **Ratings and Characteristic Curves of BAV70**



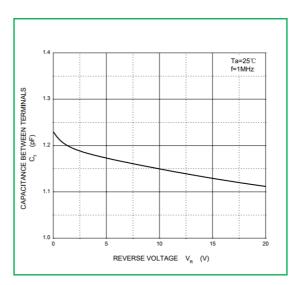
Forward Characteristics



Power Derating Curve



Reverse Characteristics



Capacitance Characteristics